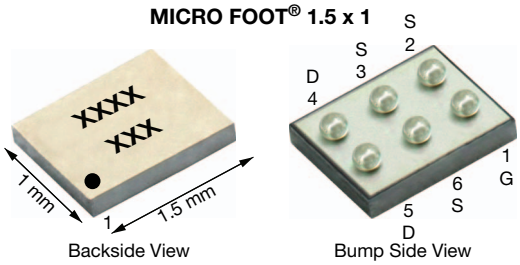
N-Channel 20 V (D-S) MOSFET

PRODUCT SUMMARY			
V_{DS} (V)	$R_{DS(on)}$ (Ω) MAX.	I_D (A)	Q_g (TYP.)
20	0.033 at V_{GS} = 4.5 V	16 [e]	7.5 nC
	0.037 at V_{GS} = 2.5 V	16 [e]	
	0.042 at V_{GS} = 1.8 V	15	

MICRO FOOT® 1.5 x 1



Backside View | Bump Side View

Marking Code: xxxx = 8406
xxx = Date / lot traceability code

Ordering Information:
Si8406DB-T2-E1 (Lead (Pb)-free and halogen-free)

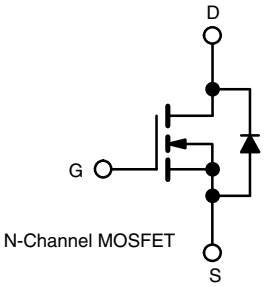
FEATURES

- TrenchFET® power MOSFET
- Ultra-small 1.5 mm x 1 mm maximum outline
- Ultra-thin 0.59 mm maximum height
- Material categorization:
  for definitions of compliance please see www.vishay.com/doc?99912

Pb-free
RoHS COMPLIANT
HALOGEN FREE Available

APPLICATIONS

- Load switch
- Battery management
- Boost converter



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C, unless otherwise noted)				
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		V_{DS}	20	V
Gate-Source Voltage		V_{GS}	± 8	
Continuous Drain Current (T_J = 150 °C)	T_C = 25 °C	I_D	16 [e]	A
	T_C = 70 °C		13.5	
	T_A = 25 °C		7.8 [a,b]	
	T_A = 70 °C		6.2 [a,b]	
Pulsed Drain Current (t = 300 µs)		I_{DM}	30	
Continuous Source-Drain Diode Current	T_C = 25 °C	I_S	11	
	T_A = 25 °C		2.3 [a,b]	
Maximum Power Dissipation	T_C = 25 °C	P_D	13	W
	T_C = 70 °C		8.4	
	T_A = 25 °C		2.77 [a,b]	
	T_A = 70 °C		1.77 [a,b]	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55 to +150	°C
Package Reflow Conditions [c]	IR/Convection		260	

Notes

a. Surface mounted on 1" x 1" FR4 board.
b. t = 10 s.
c. Refer to IPC/JEDEC® (J-STD-020), no manual or hand soldering.
d. Case in defined as the top surface of the package.
e. T_C = 25 °C package limited.

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	TYPICAL	MAXIMUM	UNIT
Maximum Junction-to-Ambient [a,b]		R_{thJA}	37	45	°C/W
Maximum Junction-to-Case (Drain) [c]	Steady State	R_{thJC}	7	9.5	

Notes

a. Surface mounted on 1" x 1" FR4 board.
b. Maximum under steady state conditions is 85 °C/W.
c. Case is defined as top surface of the package.

SPECIFICATIONS (T_J = 25 °C, unless otherwise noted)						
PARAMETER	**SYMBOL**	**TEST CONDITIONS**	**MIN.**	**TYP.**	**MAX.**	**UNIT**
Static						
Drain-Source Breakdown Voltage	V_{DS}	V_{GS} = 0, I_D = 250 µA	20	-	-	V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	I_D = 250 µA	-	18	-	mV/°C
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$		-	-3	-	
Gate-Source Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 µA	0.4	-	0.85	V
Gate-Source Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 8 V	-	-	± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 20 V, V_{GS} = 0 V	-	-	1	µA
		V_{DS} = 20 V, V_{GS} = 0 V, T_J = 70 °C	-	-	10	
On-State Drain Current [a]	$I_{D(on)}$	$V_{DS} \geq$ 5 V, V_{GS} = 4.5 V	5	-	-	A
Drain-Source On-State Resistance [a]	$R_{DS(on)}$	V_{GS} = 4.5 V, I_D = 1 A	-	0.026	0.033	Ω
		V_{GS} = 2.5 V, I_D = 1 A	-	0.028	0.037	
		V_{GS} = 1.8 V, I_D = 1 A	-	0.030	0.042	
Forward Transconductance [a]	g_{fs}	V_{DS} = 10 V, I_D = 1 A	-	20		S
Dynamic [b]						
Input Capacitance	C_{iss}	V_{DS} = 10 V, V_{GS} = 0 V, f = 1 MHz	-	830	-	pF
Output Capacitance	C_{oss}		-	146	-	
Reverse Transfer Capacitance	C_{rss}		-	61	-	
Total Gate Charge	Q_g	V_{DS} = 10 V, V_{GS} = 8 V, I_D = 1 A	-	13	20	nC
		V_{DS} = 10 V, V_{GS} = 4.5 V, I_D = 1 A	-	7.5	12	
Gate-Source Charge	Q_{gs}		-	1.1	-	
Gate-Drain Charge	Q_{gd}		-	0.8	-	
Gate Resistance	R_g	V_{GS} = 0.1 V, f = 1 MHz	-	3.6	-	Ω
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = 10 V, R_L = 10 Ω $I_D \cong$ 1 A, V_{GEN} = 4.5 V, R_g = 1 Ω	-	7	15	ns
Rise Time	t_r		-	18	40	
Turn-Off Delay Time	$t_{d(off)}$		-	30	60	
Fall Time	t_f		-	10	20	
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = 10 V, R_L = 10 Ω I_D = 1 A, V_{GEN} = 8 V, R_g = 1 Ω	-	5	10	ns
Rise Time	t_r		-	17	35	
Turn-Off Delay Time	$t_{d(off)}$		-	25	50	
Fall Time	t_f		-	10	20	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	T_C = 25 °C	-	-	20	A
Pulse Diode Forward Current	I_{SM}		-	-	30	
Body Diode Voltage	V_{SD}	I_S = 1 A, V_{GS} = 0	-	0.7	1.2	V
Body Diode Reverse Recovery Time	t_{rr}	I_F = 1 A, dI/dt = 100 A/µs, T_J = 25 °C	-	15	30	ns
Body Diode Reverse Recovery Charge	Q_{rr}		-	5	10	nC
Reverse Recovery Fall Time	t_a		-	8	-	ns
Reverse Recovery Rise Time	t_b		-	7	-	

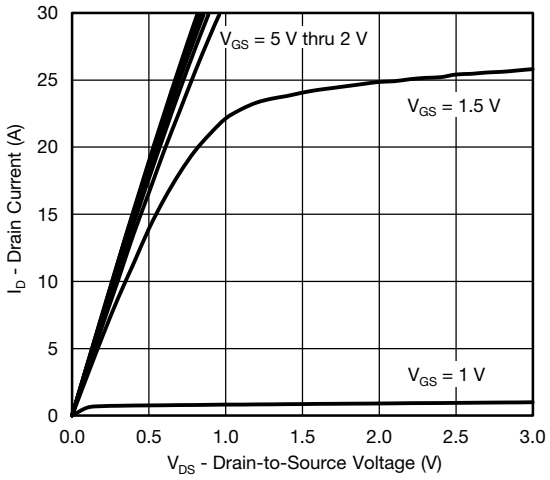
Notes

a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.

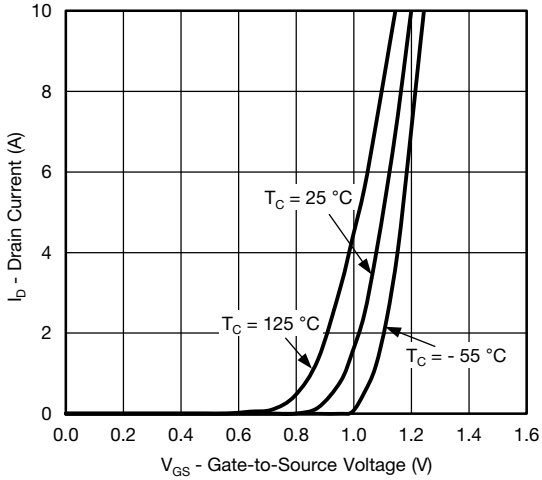
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

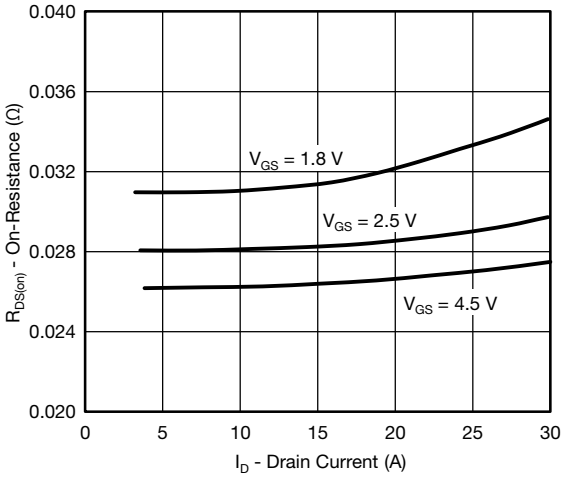
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



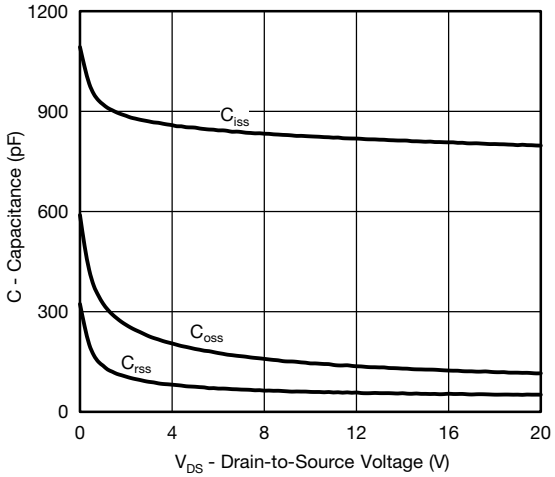
Output Characteristics



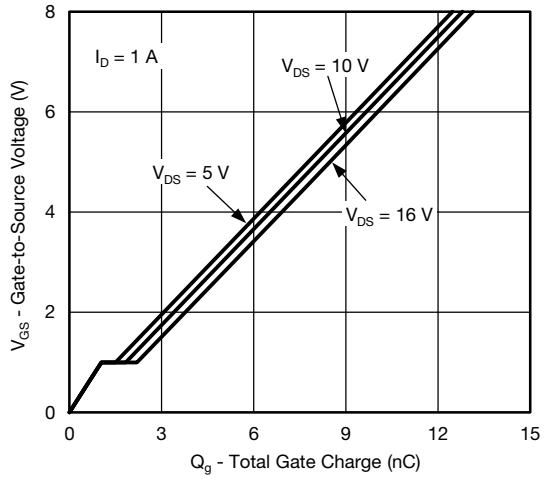
Transfer Characteristics



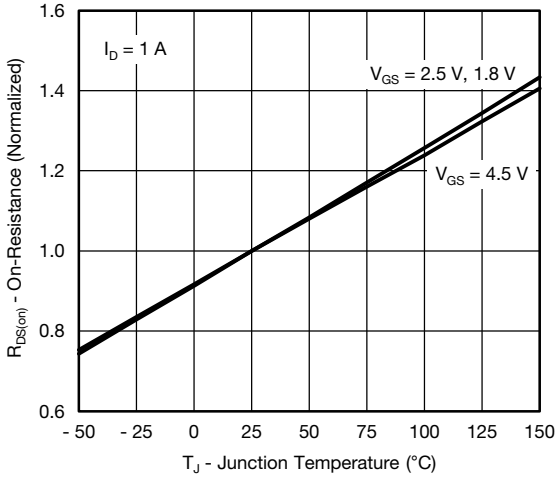
On-Resistance vs. Drain Current and Gate Voltage



Capacitance

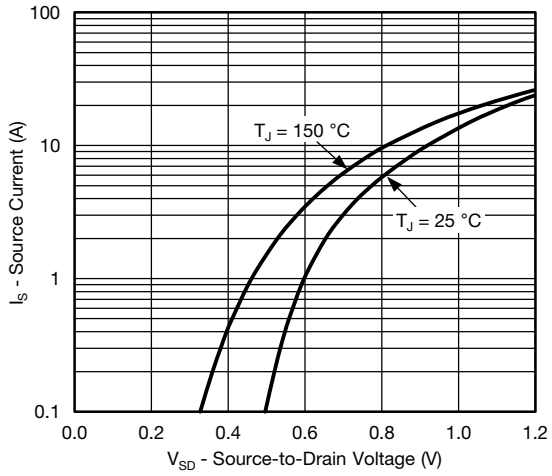


Gate Charge

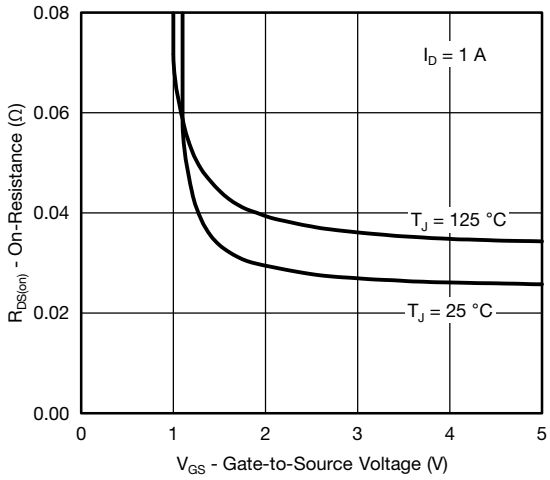


On-Resistance vs. Junction Temperature

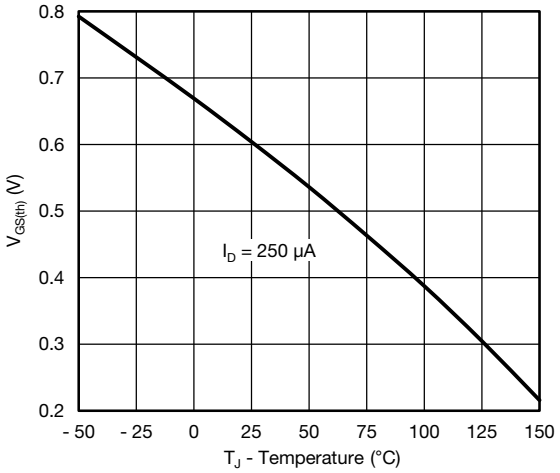
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



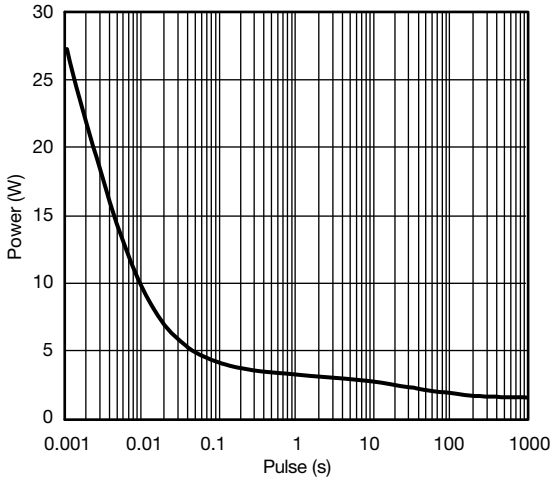
Source-Drain Diode Forward Voltage



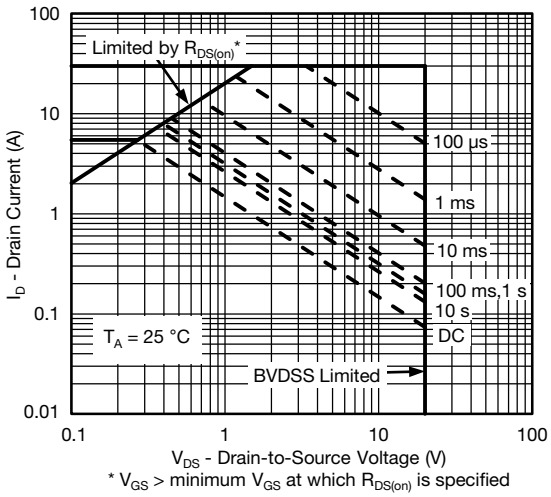
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage

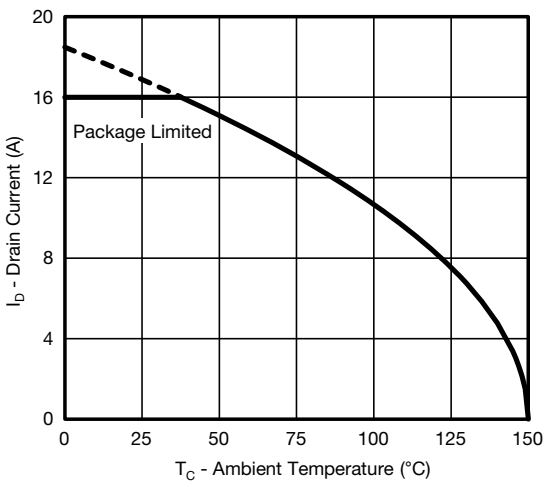


Single Pulse Power, Junction-to-Ambient

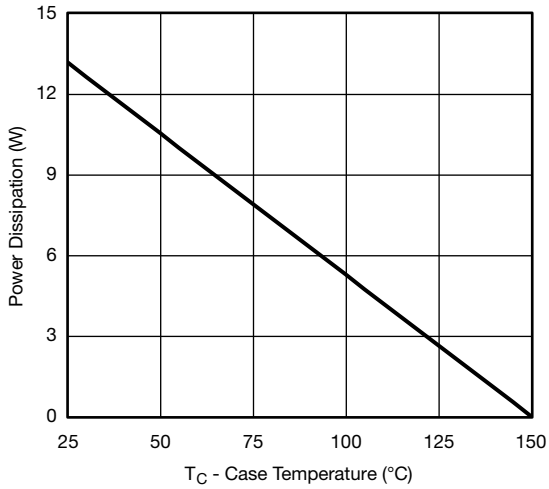


Safe Operating Area, Junction-to-Ambient

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



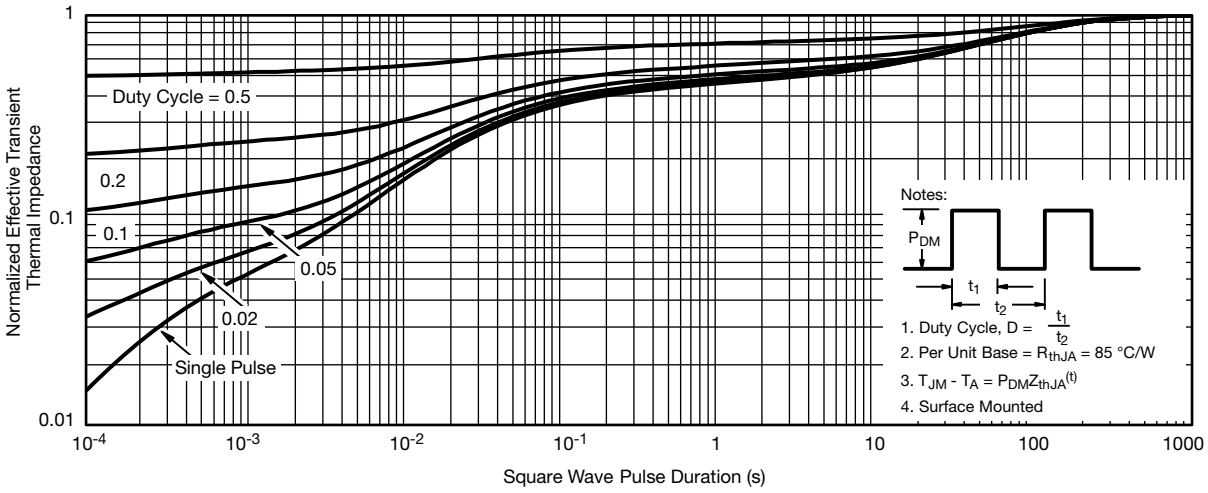
Current Derating*



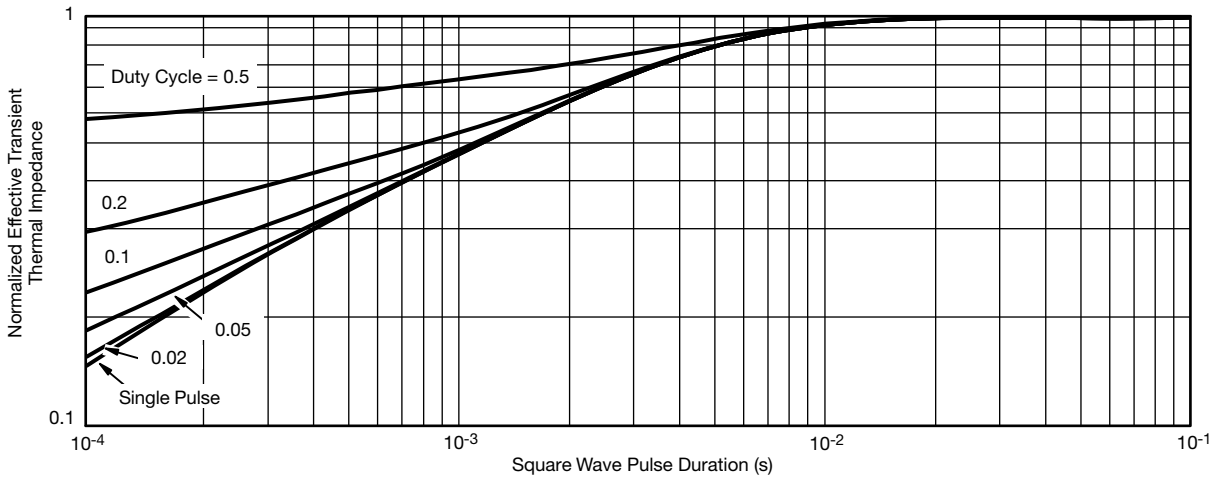
Power Derating

* The power dissipation P_D is based on $T_{J\ (max.)}$ = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



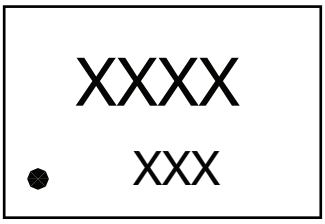
Normalized Thermal Transient Impedance, Junction-to-Ambient



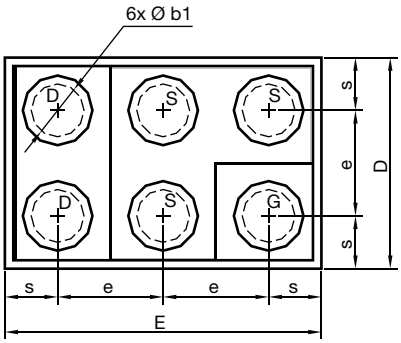
Normalized Thermal Transient Impedance, Junction-to-Case

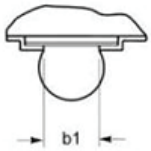
Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?62530.

MICRO FOOT®: 6-Bump
(1.5 mm x 1 mm, 0.5 mm Pitch, 0.250 mm Bump Height)

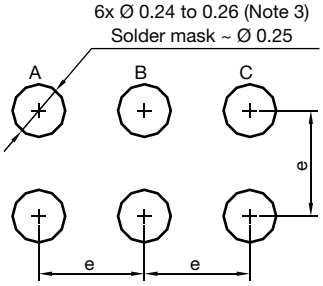


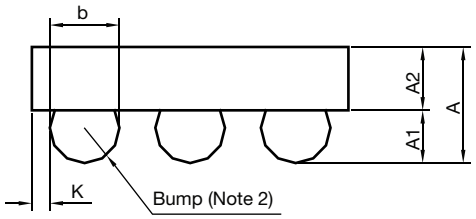
Mark on Backside of Die





NOTE 5





Recommended Land Pattern

Notes

(unless otherwise specified)

1. Six (6) solder bumps are 95.5/3.8/0.7 Sn/Ag/Cu.
2. Backside surface is coated with a Ti/Ni/Ag layer.
3. Non-solder mask defined copper landing pad.
4. Laser marks on the silicon die back.
5. “b1” is the diameter of the solderable substrate surface, defined by an opening in the solder resist layer solder mask defined.
6. • is the location of pin 1

DIM.	MILLIMETERS			INCHES		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	0.510	0.575	0.590	0.0201	0.0226	0.0232
A_1	0.220	0.250	0.280	0.0087	0.0098	0.0110
A_2	0.290	0.300	0.310	0.0114	0.0118	0.0122
b	0.297	0.330	0.363	0.0116	0.0129	0.0143
b1		0.250			0.0098	
e		0.500			0.0197	
s	0.210	0.230	0.250	0.0082	0.0090	0.0098
D	0.920	0.960	1.000	0.0362	0.0378	0.0394
E	1.420	1.460	1.500	0.0559	0.0575	0.0591
K	0.028	0.065	0.102	0.0011	0.0025	0.0040

Note

- Use millimeters as the primary measurement.

ECN: T15-0140-Rev. A, 20-Apr-15
DWG: 6035

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